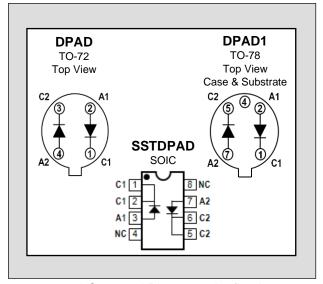


Over 30 Years of Quality Through Innovation

FEATURES						
Direct Replacement For SILICONIX DPAD SERIES						
HIGH ON ISOLATION	20fA					
EXCELLENT CAPACITANCE MATCHING ΔC _R ≤0.2pF						
ABSOLUTE MAXIMUM RATINGS ¹						
@ 25°C (unless otherwise stated)						
Maximum Temperatures						
Storage Temperature	-55°C to +150°C					
Operating Junction Temperature -55°C to +150°C						
Maximum Power Dissipation						
Continuous Power Dissipation (DPAD) ³	500mW					
Maximum Currents						
Forward Current (DPAD)	50mA					

DPAD SERIES

MONOLITHIC DUAL PICO AMPERE DIODES



^{*} Case and Pin 4 must be floating on all TO-78 case devices

COMMON ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise stated)

SYMBOL	CHARACTERISTIC			TYP.	MAX.	UNITS	CONDITIONS
	Reverse Breakdown Voltage	DPAD1	-45				I _R = -1µA
BV _R		DPAD2,5,10,20,50,100	-45			V	
		SSTDPAD5,50,100	-30				
V _F	Forward Voltage			0.8	1.5		I _F = 1mA
	Differential Capacitance	DPAD1			0.2		V _{R1} = V _{R2} = -5V, <i>f</i> =1MHz
C _{R1} - C _{R2}	(ΔC_R)	ALL OTHERS			0.5		
C _{rss}	Total Reverse Capacitance	DPAD1			0.8	pF	V _R = -5V, <i>f</i> =1MHz
		DPAD2,5,10,20,50,100			2.0		
		SSTDPAD5,50,100			4.0		

SPECIFIC ELECTRICAL CHARACTERISTICS @ 25°C (unless otherwise stated)

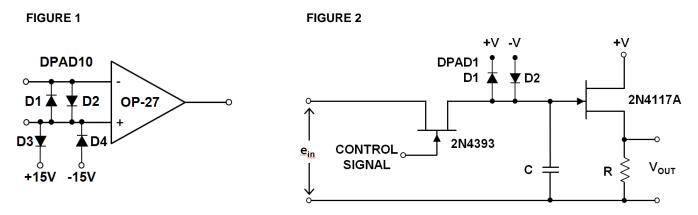
SYMBOL	CHARACTERISTIC		DPAD ²	SSTDPAD ²	UNITS	CONDITIONS
I _R	Maximum Reverse Leakage Current ²	(SST)DPAD1	-1		pA	V _R = -20V
		(SST)DPAD2	-2			
		(SST)DPAD5	-5	-5		
		(SST)DPAD10	-10			
		(SST)DPAD20	-20			
		(SST)DPAD50	-50	-50		
		(SST)DPAD100	-100	-100		

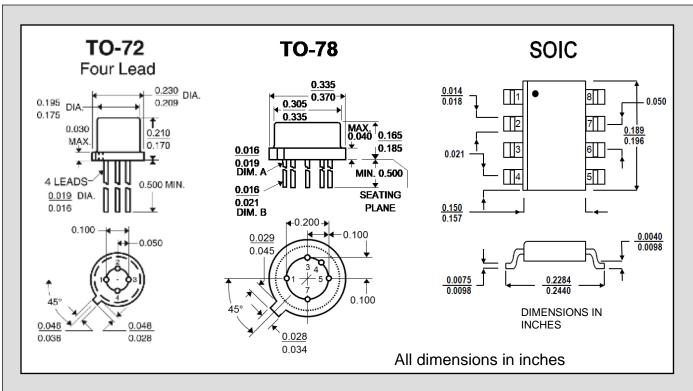
Figure 1. Operational Amplifier Protection

Input Differential Voltage limited to 0.8V (typ) by DPADs D_1 and D_2 . Common Mode Input voltage limited by DPADs D_3 and D_4 to $\pm 15V$.

Figure 2. Sample and Hold Circuit

Typical Sample and Hold circuit with clipping. DPAD diodes reduce offset voltages fed capacitively from the JFET switch gate.





- 1. Absolute maximum ratings are limiting values above which serviceability may be impaired.
- 2. The DPAD type number denotes its maximum reverse current value in pico amperes. Devices with I_R values intermediate to those shown are available upon request.
- 3. Derate 4 mW/°C above 25°C

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